

Notice of Reference CitedApplication/Control No.
09/993,771Applicant(s)/Patent Under Reexam
Hasegawa et alExaminer
Savitri MulpuriArt Unit
2812

Page 1 of 1

U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	2002/0167018	11/02	Nakamura et al	257	103
B	5,757,835	5/98	Ono et al	372	46
C	2002/0001864	1/02	Ishijikawa et al	438	22
D	6,323,052	11/01	Horie et al	438	46
E	5,583,880	12/96	Shakuda	372	46
F	6,238,947	5/01	Sahkuda	438	94
G					
H					
I					
J					
K					
L					
M					

FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
N						
O						
P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Chen et al, "Electrical and optical cahnges in the surface of reactvely ion etched n-GaN" Soild-state el;ectronics 43 (1999)649-652
V	Yang et al, "Effectiveness of multiple-pair buffer layer to improve the GaN layers grown by metallorganic chemical vapor deposition" Journal of Applied Physics Vol. 85, Number 12, pp 8427-8431)
W	
X	

¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.